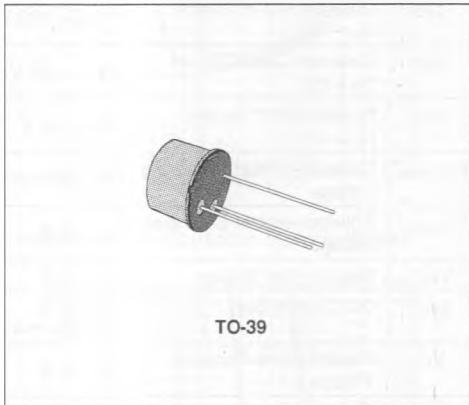
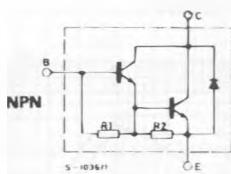
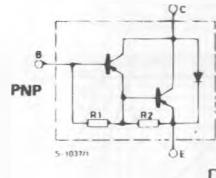


MEDIUM POWER DARLINGTON

DESCRIPTION

The BDW91 is a silicon epitaxial base NPN transistor in monolithic Darlington configuration mounted in Jedec TO-39 metal case. It is intended for use in switching and linear applications. The complementary PNP type is the BDW92.


INTERNAL SCHEMATIC DIAGRAMS

 S-1036f
 R1 Typ. 10k Ω
 R2 Typ. 150 Ω

 S-1037f
 R1 Typ. 10k Ω
 R2 Typ. 150 Ω
ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base Voltage ($I_E = 0$)	180	V
V_{CEO}	Collector-emitter Voltage ($I_B = 0$)	180	V
V_{EBO}	Emitter-base Voltage ($I_C = 0$)	6	V
I_C	Collector Current	4	A
I_B	Base Current	100	mA
P_{tot}	Total Power Dissipation at $T_{case} \leq 25^\circ\text{C}$ $T_{amb} \leq 25^\circ\text{C}$	10 1	W W
T_{stg}	Storage Temperature	-65 to 200	°C
T_j	Junction Temperature	200	°C

For PNP type voltage and current values are negative.

THERMAL DATA

$R_{th\text{-case}}$	Thermal Resistance Junction-case	Max	17.5	$^{\circ}\text{C}/\text{W}$
$R_{th\text{-amb}}$	Thermal Resistance Junction-ambient	Max	175	$^{\circ}\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_{\text{case}} = 25^{\circ}\text{C}$ unless otherwise specified)

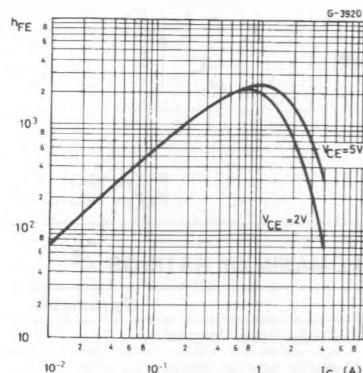
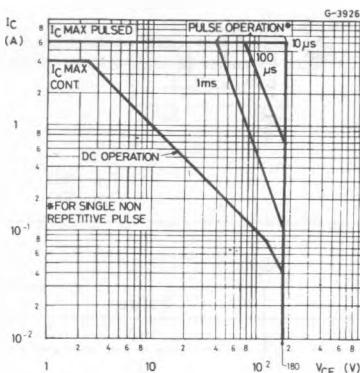
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cutoff Current ($I_E = 0$)	$V_{CB} = 180 \text{ V}$			50	μA
I_{CEO}	Collector Cutoff Current ($I_B = 0$)	$V_{CE} = 90 \text{ V}$			50	μA
I_{EBO}	Emitter Cutoff Current ($I_C = 0$)	$V_{EB} = 6 \text{ V}$	0.4		2	mA
$V_{CEO(\text{sus})}^*$	Collector-emitter Sustaining Voltage	$I_C = 50 \text{ mA}$	180			V
$V_{CE(\text{sat})}^*$	Collector-emitter Saturation Voltage	$I_C = 2 \text{ A}$	$I_B = 4 \text{ mA}$		2	V
V_{BE}^*	Base-emitter Voltage	$I_C = 2 \text{ A}$	$V_{CE} = 2 \text{ V}$		2.5	V
h_{FE}^*	DC Current Gain	$I_C = 2 \text{ A}$ $I_C = 50 \text{ mA}$	$V_{CE} = 5 \text{ V}$ $V_{CE} = 5 \text{ V}$	1000 150	3000 300	
V_F^*	Parallel Diode Forward Voltage	$I_F = 2 \text{ A}$			2.5	V
h_{fe}	Small Signal Current Gain	$I_C = 0.5 \text{ A}$ $f = 1 \text{ MHz}$	$V_{CE} = 2 \text{ V}$	20		

* Pulsed : pulse duration = 300 μsec , duty cycle = 1 %.

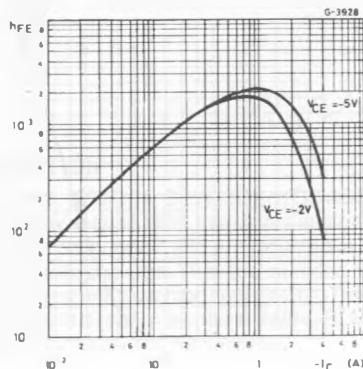
For PNP type voltage and current values are negative

Safe Operating Area.

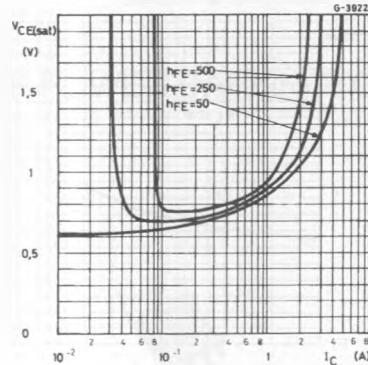
DC Current Gain (BDW91).



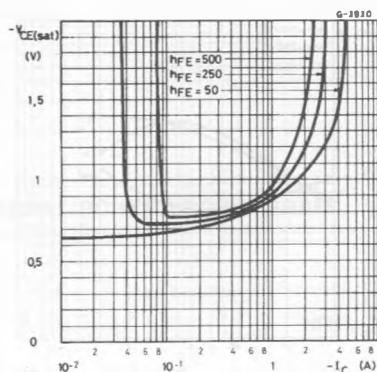
DC Current Gain (BDW92)



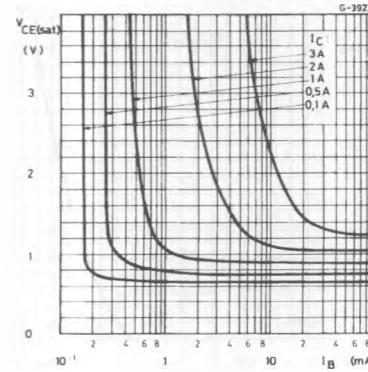
Collector-emitter Saturation Voltage (BDW91)



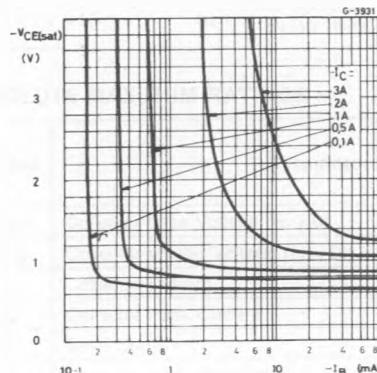
Collector-emitter Saturation Voltage (BDW92)



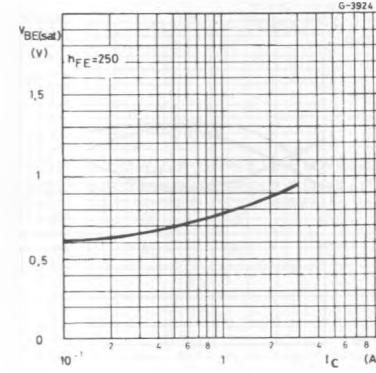
Collector-emitter Saturation Voltage (BDW91)



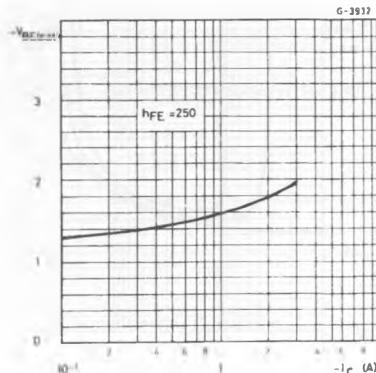
Collector-emitter Saturation Voltage (BDW92)



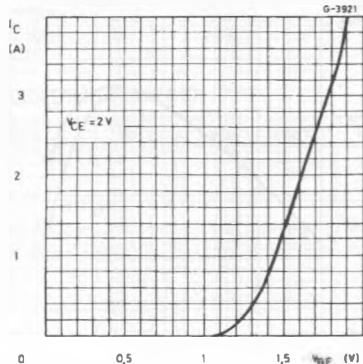
Base-emitter Saturation Voltage (BDW91)



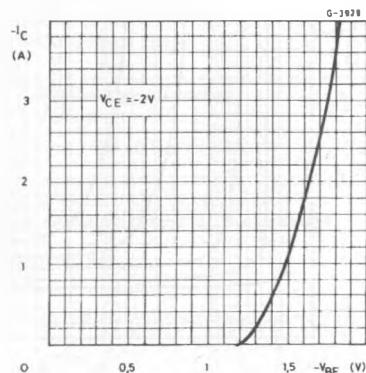
Base-emitter Saturation Voltage (BDW92)



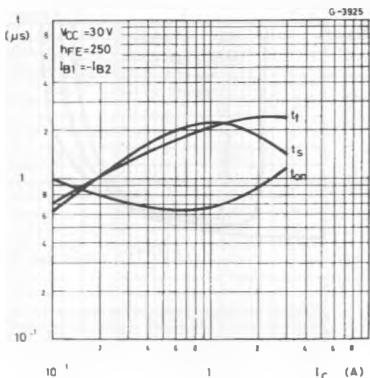
DC Transconductance (BDW91)



DC Transconductance (BDW92)



Saturated Switching Characteristics (BDW91)



Saturated Switching Characteristics (BDW92)

